25AA640A/25LC640A

64K SPI Bus Serial EEPROM

Device Selection Table

Part Number	Vcc Range	Page Size	Temp. Ranges	Packages
25LC640A	2.5-5.5V	32 Byte	I,E	P, SN, ST, MS, MF, MNY
25AA640A	1.8-5.5V	32 Byte	I	P, SN, ST, MS, MF, MNY

Features:

- Max. Clock 10 MHz
- Low-Power CMOS Technology
  - Max. Write Current: 5 mA at 5.5V, 10 MHz
  - Read Current: 5 mA at 5.5V, 10 MHz
  - Standby Current: 1 μA at 5.5V
- 8192 x 8-bit Organization
- 32 Byte Page
- Self-Timed Erase and Write Cycles (5 ms max.)
- Block Write Protection
  - Protect none, 1/4, 1/2 or all of array
- Built-In Write Protection
  - Power-on/off data protection circuitry
  - Write enable latch
  - Write-protect pin
- Sequential Read
- High Reliability
  - Endurance: 1,000,000 erase/write cycles
  - Data retention: > 200 years
  - ESD protection: > 4000V
- Temperature Ranges Supported:
  - Industrial (I): -40°C to +85°C
  - Automotive (E): -40°C to +125°C

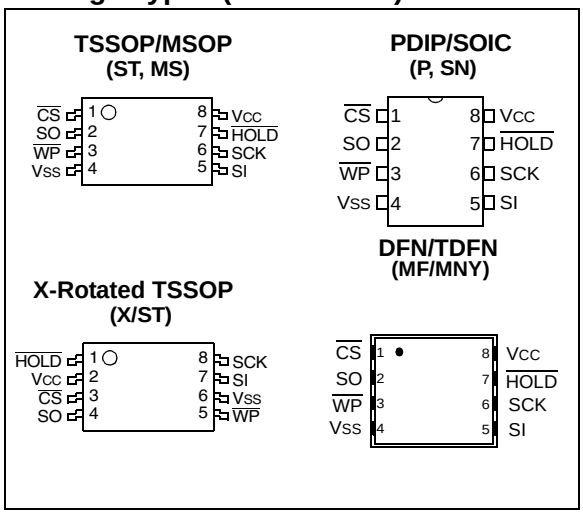
Description:

The Microchip Technology Inc. 25AA640A/25LC640A (25XX640A*) are 64 kbit Serial Electrically Erasable PROMs. The memory is accessed via a simple Serial Peripheral Interface (SPI) compatible serial bus. The bus signals required are a clock input (SCK) plus separate data in (SI) and data out (SO) lines. Access to the device is controlled through a Chip Select (CS) input.

Communication to the device can be paused via the hold pin (HOLD). While the device is paused, transitions on its inputs will be ignored, with the exception of Chip Select, allowing the host to service higher priority interrupts.

The 25XX640A is available in standard packages including 8-lead PDIP and SOIC, and advanced packaging including 8-lead MSOP, 8-lead TSSOP, DFN and TDFN.

Package Types (not to scale)



* 25XX640A is used in this document as a generic part number for the 25AA640A, 25LC640A devices.

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings(†)

V_{CC}.....6.5V

All inputs and outputs w.r.t. V_{SS} ..... -0.6V to V_{CC} +1.0V

Storage temperature .....-65°C to 150°C

Ambient temperature under bias.....-40°C to 125°C

ESD protection on all pins.....4 kV

† NOTICE**:** Stresses above those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for an extended period of time may affect device reliability.

TABLE 1-1: DC CHARACTERISTICS

DC CHARACTERISTICS			Industrial (I): T_A = -40°C to +85°C V_{CC} = 1.8V to 5.5V Automotive (E): T_A = -40°C to +125°C V_{CC} = 2.5V to 5.5V			
Param. No.	**Sym.**	**Characteristic**	**Min.**	**Max.**	**Units**	**Test Conditions**
D001	V_{IH1}	High-level input voltage	.7 V_{CC}	V_{CC} +1	V	
D002	V_{IL1}	Low-level input voltage	-0.3	0.3 V_{CC}	V	$V_{CC} \geq$ 2.7V
D003	V_{IL2}		-0.3	0.2 V_{CC}	V	V_{CC} < 2.7V
D004	V_{OL}	Low-level output voltage	—	0.4	V	I_{OL} = 2.1 mA
D005	V_{OL}		—	0.2	V	I_{OL} = 1.0 mA, V_{CC} < 2.5V
D006	V_{OH}	High-level output voltage	V_{CC} -0.5	—	V	I_{OH} = -400 µA
D007	I_{LI}	Input leakage current	—	±1	µA	$\overline{CS}$ = V_{CC}, V_{IN} = V_{SS} or V_{CC}
D008	I_{LO}	Output leakage current	—	±1	µA	$\overline{CS}$ = V_{CC}, V_{OUT} = V_{SS} or V_{CC}
D009	C_{INT}	Internal Capacitance (all inputs and outputs)	—	7	pF	T_A = 25°C, CLK = 1.0 MHz, V_{CC} = 5.0V **(Note)**
D010	I_{CC} Read	Operating Current	— —	5 2.5	mA mA	V_{CC} = 5.5V; F_{CLK} = 10.0 MHz; SO = Open V_{CC} = 2.5V; F_{CLK} = 5.0 MHz; SO = Open
D011	I_{CC} Write		— —	5 3	mA mA	V_{CC} = 5.5V V_{CC} = 2.5V
D012	I_{CCS}	Standby Current	— —	5 1	µA µA	$\overline{CS}$ = V_{CC} = 5.5V, Inputs tied to V_{CC} or V_{SS}, 125°C $\overline{CS}$ = V_{CC} = 5.5V, Inputs tied to V_{CC} or V_{SS}, 85°C

Note: This parameter is periodically sampled and not 100% tested.

TABLE 1-2: AC CHARACTERISTICS

AC CHARACTERISTICS			Industrial (I): TA = -40°C to +85°C VCC = 1.8V to 5.5V Automotive (E): TA = -40°C to +125°C VCC = 2.5V to 5.5V			
Param. No.	**Sym.**	**Characteristic**	**Min.**	**Max.**	**Units**	**Test Conditions**
1	FCLK	Clock frequency	— — —	10 5 3	MHz MHz MHz	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
2	TCSS	$\overline{CS}$ setup time	50 100 150	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
3	TCSH	$\overline{CS}$ hold time	100 200 250	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
4	TCSD	$\overline{CS}$ disable time	50	—	ns	—
5	Tsu	Data setup time	10 20 30	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
6	THD	Data hold time	20 40 50	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
7	TR	CLK rise time	—	100	ns	**(Note 1)**
8	TF	CLK fall time	—	100	ns	**(Note 1)**
9	THI	Clock high time	50 100 150	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
10	TLO	Clock low time	50 100 150	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
11	TCLD	Clock delay time	50	—	ns	—
12	TCLE	Clock enable time	50	—	ns	—
13	TV	Output valid from clock low	— — —	50 100 160	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
14	THO	Output hold time	0	—	ns	**(Note 1)**
15	TDIS	Output disable time	— — —	40 80 160	ns ns ns	4.5V ≤ Vcc ≤ 5.5V**(Note 1)** 2.5V ≤ Vcc ≤ 4.5V**(Note 1)** 1.8V ≤ Vcc ≤ 2.5V**(Note 1)**
16	THS	$\overline{HOLD}$ setup time	20 40 80	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V

Note 1: This parameter is periodically sampled and not 100% tested.

2: This parameter is not tested but ensured by characterization. For endurance estimates in a specific application, please consult the Total Endurance™ Model which can be obtained from Microchip's web site

3: TWC begins on the rising edge of $\overline{CS}$ after a valid write sequence and ends when the internal write cycle is complete.

TABLE 1-2: AC CHARACTERISTICS (CONTINUED)

AC CHARACTERISTICS			Industrial (I): TA = -40°C to +85°C VCC = 1.8V to 5.5V Automotive (E): TA = -40°C to +125°C VCC = 2.5V to 5.5V			
Param. No.	**Sym.**	**Characteristic**	**Min.**	**Max.**	**Units**	**Test Conditions**
17	THH	$\overline{HOLD}$ hold time	20 40 80	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
18	THZ	$\overline{HOLD}$ low to output High-Z	30 60 160	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V**(Note 1)** 2.5V ≤ Vcc < 4.5V**(Note 1)** 1.8V ≤ Vcc < 2.5V**(Note 1)**
19	THV	$\overline{HOLD}$ high to output valid	30 60 160	— — —	ns ns ns	4.5V ≤ Vcc ≤ 5.5V 2.5V ≤ Vcc < 4.5V 1.8V ≤ Vcc < 2.5V
20	TWC	Internal write cycle time	—	5	ms	**(NOTE 3)**
21	—	Endurance	1M	—	E/W Cycles	**(NOTE 2)**

Note 1: This parameter is periodically sampled and not 100% tested.

2: This parameter is not tested but ensured by characterization. For endurance estimates in a specific application, please consult the Total Endurance™ Model which can be obtained from Microchip's web site

3: TWC begins on the rising edge of $\overline{CS}$ after a valid write sequence and ends when the internal write cycle is complete.

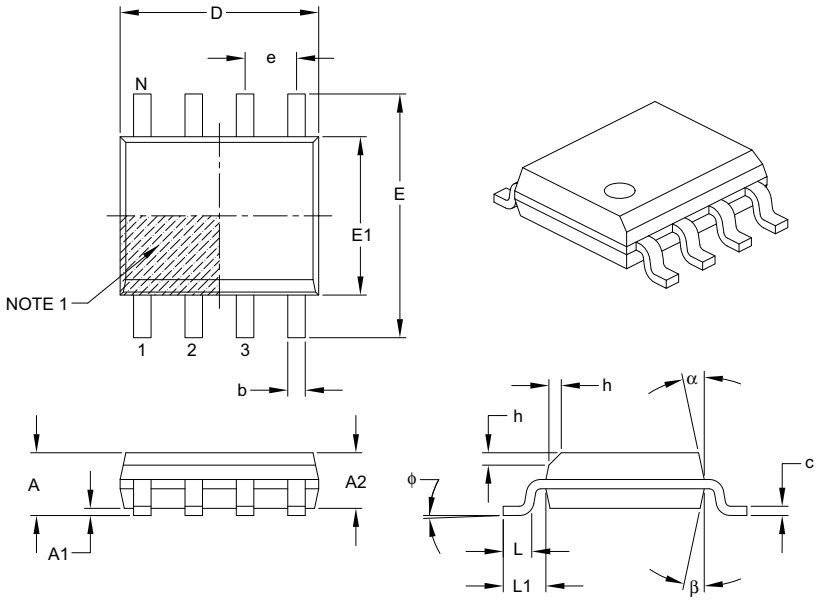
TABLE 1-3: AC TEST CONDITIONS

AC Waveform:	
VLO = 0.2V	—
VHI = VCC - 0.2V	**(Note 1)**
VHI = 4.0V	**(Note 2)**
CL = 100 pF	**—**
Timing Measurement Reference Level	
Input	0.5 VCC
Output	0.5 VCC

Note 1: For VCC ≤ 4.0V

2: For VCC > 4.0V

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]



Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Number of Pins	N		8	
Pitch	e		1.27 BSC	
Overall Height	A	–	–	1.75
Molded Package Thickness	A2	1.25	–	–
Standoff §	A1	0.10	–	0.25
Overall Width	E		6.00 BSC	
Molded Package Width	E1		3.90 BSC	
Overall Length	D		4.90 BSC	
Chamfer (optional)	h	0.25	–	0.50
Foot Length	L	0.40	–	1.27
Footprint	L1		1.04 REF	
Foot Angle	φ	0°	–	8°
Lead Thickness	c	0.17	–	0.25
Lead Width	b	0.31	–	0.51
Mold Draft Angle Top	α	5°	–	15°
Mold Draft Angle Bottom	β	5°	–	15°

Notes:

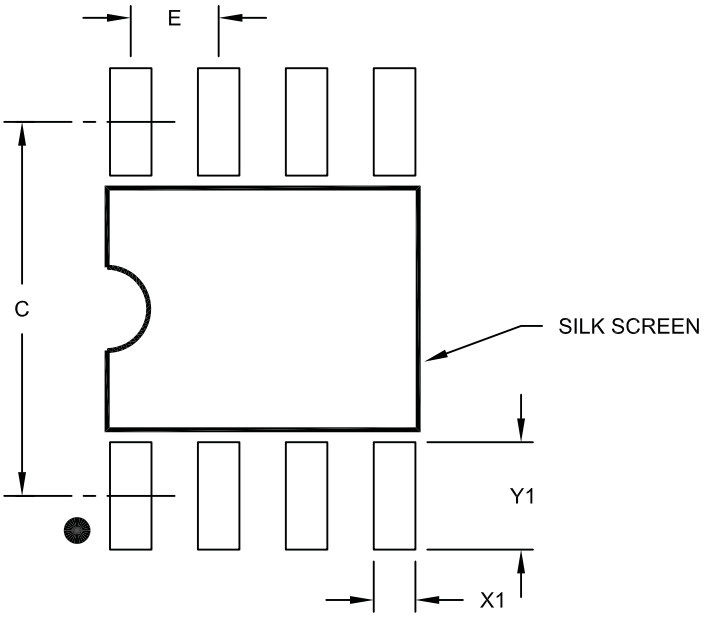
1. Pin 1 visual index feature may vary, but must be located within the hatched area.
2. § Significant Characteristic.
3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15 mm per side.
4. Dimensioning and tolerancing per ASME Y14.5M.

   BSC: Basic Dimension. Theoretically exact value shown without tolerances.

   REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-057B

8-Lead Plastic Small Outline (SN) – Narrow, 3.90 mm Body [SOIC]



RECOMMENDED LAND PATTERN

Units		MILLIMETERS		
Dimension Limits		MIN	NOM	MAX
Contact Pitch	E		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)	Y1			1.55

Notes:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2057A

PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	X	–	X	/XX
Device	Tape & Reel		Temp Range	Package

Device:	25AA640A	=	64k-bit, 1.8V, SPI Serial EEPROM
	25LC640A	=	64k-bit, 2.5V, SPI Serial EEPROM
	25AA640AX	=	64k-bit, 1.8V, SPI Serial EEPROM in alternate pinout (ST only)
	25LC640AX	=	64k-bit, 2.5V, SPI Serial EEPROM in alternate pinout (ST only)
Tape & Reel:	Blank	=	Standard packaging
	T	=	Tape & Reel
Temperature Range:	I	=	-40°C to+85°C
	E	=	-40°C to+125°C
Package:	MS	=	Plastic MSOP (Micro Small Outline), 8-lead
	P	=	Plastic DIP (300 mil body), 8-lead
	SN	=	Plastic SOIC (3.90 mm body), 8-lead
	ST	=	TSSOP (4.4 mm body), 8-lead
	MF	=	DFN (5x6), 8-lead
	MNY(1)	=	TDFN (2x3), 8-lead

Note 1: "Y" indicates a Nickel Palladium Gold (NiPdAu) finish.

Examples:

a) 25AA640A-I/MS = 64 kbit, 1.8V Serial EEPROM, Industrial temp., MSOP package

b) 25AA640AT-I/SN = 6 kbit, 1.8V Serial EEPROM, Industrial temp., Tape & Reel, SOIC package

c) 25LC640AT-E/SN = 64 kbit, 2.5V Serial EEPROM, Extended temp., Tape & Reel, SOIC package

d) 25LC640AT-I/ST = 64 kbit, 2.5V Serial EEPROM, Industrial temp., Tape & Reel, TSSOP package

e) 25LC640AXT-I/ST = 64 kbit, 2.5V Serial EEPROM, Industrial temp., Tape & Reel, Rotated pinout, TSSOP package